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(54) **MICROPORES AND METHODS OF MAKING AND USING THEREOF**

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(52) **U.S. Cl.**
USPC **216/56; 216/2; 216/41; 216/83**

(58) **Field of Classification Search**
None

See application file for complete search history.

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(57) **ABSTRACT**

Disclosed herein are methods of making micropores of a desired height and/or width between two isotropic wet etched features in a substrate which comprises single-level isotropic wet etching the two features using an etchant and a mask distance that is less than 2x a set etch depth. Also disclosed herein are methods using the micropores and microfluidic devices comprising the micropores.

15 Claims, 16 Drawing Sheets

